OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698

Features:

- High current transfer ratio
- Low-cost plastic package
- T-1 package style with three current range selections (OPS665, OPS666, OPS667)
- Lateral side-looking clear plastic package (OPS690, OPS691, OPS692, OPS693 and OPS695, OPS696, OPS697, OPS698)





Description:

Each LED/Photosensor pair in the series consists of a gallium arsenide infrared emitting diode and a NPN silicon phototransistor, mounted in a T-1 package (OPS665, OPS666, OPS667) or in a matched lateral side-looking plastic package (OPS690, OPS691, OPS692, OPS693 and OPS695, OPS696, OPS697, OPS698).

Matched pairs are desirable where the application is unique and the quantity required does not justify assembly tooling costs. If separation between the LED and sensor is greater than two times the specified $IC_{(ON)}$ distance, proper alignment becomes critical. Although sold as pairs, emitters and sensors are packaged separately for handling ease.

Please note that the sensor is sensitive to ambient light.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor

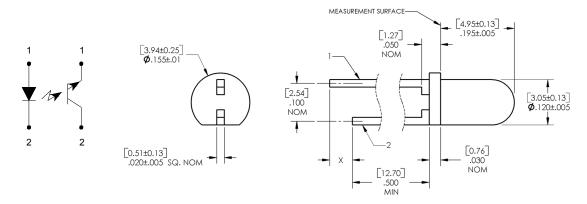
Ordering Information				
Part Number	Output	Package Style	Description	Lead Length
OPS665	Transistor	T-1	Gallium arsenide infrared emitting diode (OP165) NPN silicon phototransistor (OP505)	0.50" (`1.700 mm)
OPS666	Transistor	T-1	Gallium arsenide infrared emitting diode (OP165) NPN silicon phototransistor (OP505)	0.50" (`1.700 mm)
OPS667	Transistor	T-1	Gallium arsenide infrared emitting diode (OP165) NPN silicon phototransistor (OP505)	0.50" (`1.700 mm)
OPS690	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS691	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS692	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS693	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS695	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP145) NPN silicon phototransistor (OP555)	0.50" (`1.700 mm)
OPS696	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP145) NPN silicon phototransistor (OP555)	0.50" (`1.700 mm)
OPS697	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP145) NPN silicon phototransistor (OP555)	0.50" (`1.700 mm)
OPS698	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP145) NPN silicon phototransistor (OP555)	0.50" (`1.700 mm)



OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698



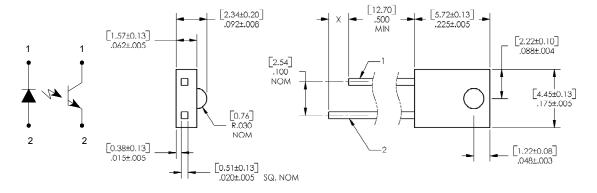
OPS665, OPS666, OPS667



DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Pin#	LED & Diode X=0.060" (1.5	Transistor X=0" (0.0 mm)
1	Anode	Emitter
2	Cathode	Collector

OPS690, OPS691, OPS692, OPS693



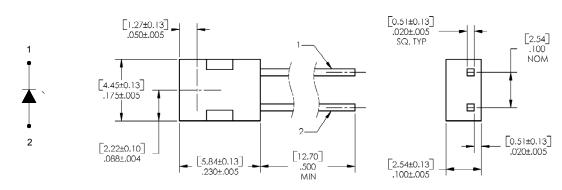
DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Pin#	LED X=0.060" (1.5	Sensor X=0" (0.0 mm)
1	Cathode	Emitter/Anode
2	Anode	Collector/Cathode

OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698



OPS695, OPS696, OPS697, OPS698



DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Pin#	Diode		
1	Cathode		
2	Anode		

OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698



Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Absolute Maximum Natings (14 - 25 Culless otherwise noted)	
Storage & Operating Temperature Range	-40°C to +100°C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron]	260°C ⁽¹⁾
Input Diode	
Forward DC Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Reverse DC Voltage	2.0 V
Power Dissipation	100 mW ⁽²⁾
Output Photosensor (OPS665/666/667) or Output Phototransistor (OPS690/691/692/693/695/696/697/698)	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW ⁽²⁾

OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698



Electrical Specifications

Electrical Characteristics (T _A = 25° C unless otherwise noted)						
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode	2	'				
V _F	Forward Voltage	-	-	1.6	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V
Output Ph	nototransistor	'				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _C = 100 μA, E _E = 0
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0	-	-	V	$I_E = 100 \mu A, E_E = 0$
I _{CEO}	Collector-Emitter Dark Current OPS665/666/667 OPS690/691/692/693 OPS695/696/697/698	- - -	- - -	100 100 100	nA nA nA	$V_{CE} = 15 \text{ V}, I_F = 0, I_E = 0$ $V_{CE} = 10 \text{ V}, I_F = 0, I_E = 0$ $V_{CE} = 10 \text{ V}, I_F = 0, I_E = 0$
Combined	i					
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OPS665/666/667 OPS690/691/692/693 OPB695/696/697/698	- - -	- - -	- 0.4 0.4	- V V	$I_F = 20 \text{ mA}, I_C = 50 \mu A^{(3)}$ $I_F = 20 \text{ mA}, I_C = 50 \mu A^{(3)}$
I _{C(ON)}	On-State Collector Current OPS665 OPS666 OPS667 OPS690, OPS695 OPS691, OPS696 OPS692, OPS697 OPS693, OPS698	0.5 1.0 5.0 100 500 1.0 2.0	- - - - -	- - - - -	mA mA mA μA μA mA mA	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}^{(3)}$ $V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}^{(3)}$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Distance from lens tip to lens tip is 0.250" (6.35 mm) OPS665, OPS666, OPS667 Distance from lens tip to lens tip is 0.125" (3.175 mm) - OPS690 thru OPS698

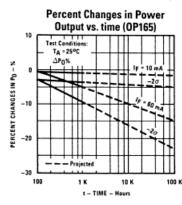
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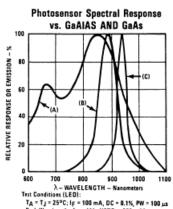
OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698



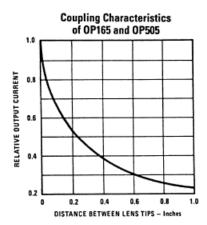
Performance

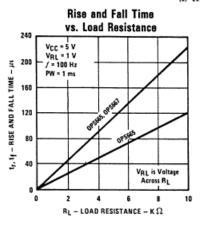
OPS665, OPS666, OPS667

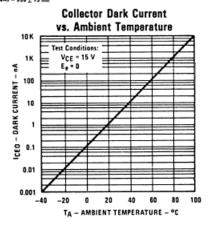


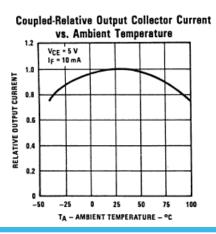


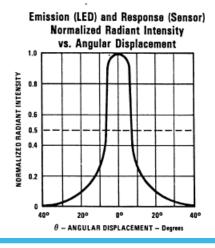
TA = T₃ = 25°C; I_F = 100 mA, DC = 0.1%, PW = 100 μs Peak Wavelength - λρ: (A) XSTR = 850 ± 30 nm (B) LED GaAIAs = 890 ± 20 nm (C) LEO GaAS = 930 ± 15 nm

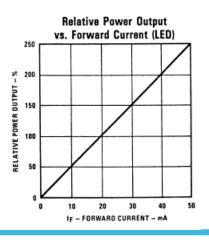










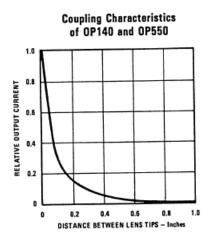


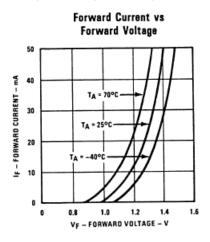
OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698

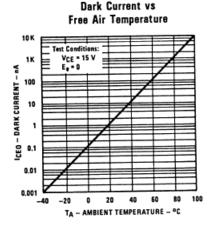


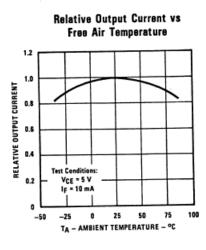
Performance

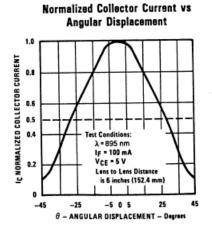
OPS690, OPS691, OPS692, OPS693

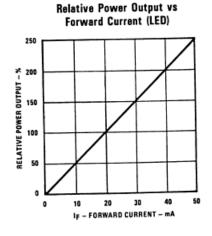










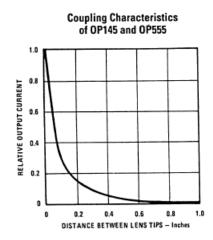


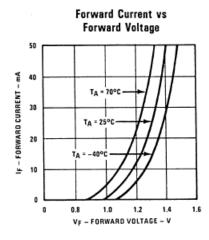
OPS665, OPS666, OPS667 OPS690, OPS691, OPS692, OPS693 OPS695, OPS696, OPS697, OPS698

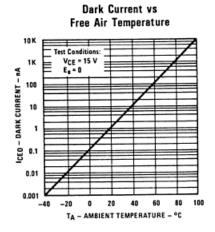


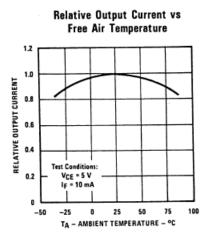
Performance

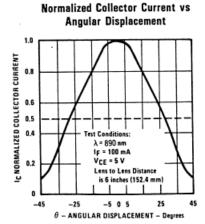
OPS695, OPS696, OPS697, OPS698

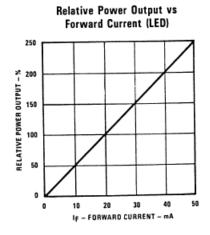












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